

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-12 (Canceled).

13. (Currently Amended) A method of manufacturing a semiconductor device comprising:
forming ~~a resist pattern~~ a plurality of first resist patterns by discharging a composition containing a photosensitizer on a first conductive layer under reduced pressure;

~~irradiating the resist pattern~~ exposing the plurality of first resist patterns through a photomask
by irradiation with of light using a photomask, within the light having a photosensitive wavelength region of the photosensitizer;

developing the irradiated plurality of first resist patterns to form a plurality of second resist patterns;

etching the first conductive layer by using ~~the resist pattern~~ the plurality of second resist patterns as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;

removing ~~the resist pattern~~ the plurality of second resist patterns on the first conductive layer;

forming an insulating film over the plurality of gate wirings;

forming a plurality of semiconductor islands over the gate electrodes with said insulating film interposed therebetween;

forming ~~a resist pattern~~ a plurality of third resistant patterns by discharging a composition containing a photosensitizer on a second conductive layer under reduced pressure;

~~irradiating the resist pattern~~ exposing the plurality of third resist patterns through a

~~photomask by irradiation with of light using a photomask, within the light having~~ a photosensitive wavelength region of the photosensitizer;

~~developing the irradiated plurality of third resist patterns to form a plurality of fourth resist patterns;~~

etching the second conductive layer by using ~~the resist pattern~~ the plurality of fourth resist patterns as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing ~~the resist pattern~~ the plurality of fourth resist patterns on the second conductive layer;

forming ~~a resist pattern~~ a plurality of fifth resist patterns by discharging a composition containing a photosensitizer on a third conductive layer under reduced pressure;

~~irradiating the resist pattern exposing the plurality of fifth resist patterns through a photomask by irradiation with of light using a photomask, within the light having~~ a photosensitive wavelength region of the photosensitizer;

~~developing the irradiated plurality of fifth resist patterns to form a plurality of sixth resist patterns;~~

etching the third conductive layer by using ~~the resist pattern~~ the plurality of sixth resist patterns as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing ~~the resist pattern~~ the plurality of sixth resist patterns on the third conductive layer.

14. (Previously Presented) A method of manufacturing a semiconductor device according to claim 13, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

15. (Previously Presented) A method of manufacturing a semiconductor device according to claim 13, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

16. (Currently Amended) A method of manufacturing a semiconductor device comprising:
forming ~~a resist pattern~~ a plurality of first resist patterns by discharging a composition containing a photosensitizer on a first conductive layer under reduced pressure;
~~irradiating the resist pattern exposing the plurality of first resist patterns through a photomask~~
by irradiation with of light using a photomask, within the light having a photosensitive wavelength
region of the photosensitizer;
developing the irradiated plurality of first resist patterns to form a plurality of second resist patterns;
etching the first conductive layer by using ~~the resist pattern~~ the plurality of second resist patterns as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;
removing ~~the resist pattern~~ the plurality of second resist patterns on the first conductive layer;
forming an insulating film over the plurality of gate wirings;
forming a plurality of first semiconductor islands over the gate electrodes with said insulating film interposed therebetween;
forming each of a plurality of channel protective layers over each of the plurality of first semiconductor islands;
forming a plurality of second semiconductor islands over the plurality of first semiconductor islands with the plurality of channel protective layers interposed therebetween;

forming ~~a resist pattern~~ a plurality of third resist patterns by discharging a composition containing a photosensitizer on a second conductive layer under reduced pressure;

~~irradiating the resist pattern~~ exposing the plurality of third resist patterns through a photomask by irradiation with of light using a photomask, within the light having a photosensitive wavelength region of the photosensitizer;

developing the irradiated plurality of third resist patterns to form a plurality of fourth resist patterns:

etching the second conductive layer by using ~~the resist pattern~~ the plurality of fourth resist patterns as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing ~~the resist pattern~~ the plurality of fourth resist patterns on the second conductive layer;

forming ~~the resist pattern~~ a plurality of fifth resist patterns by discharging a composition containing a photosensitizer on a third conductive layer under reduced pressure;

~~irradiating the resist pattern~~ exposing the plurality of fifth resist patterns through a photomask by irradiation with of light using a photomask, within the light having a photosensitive wavelength region of the photosensitizer;

developing the irradiated plurality of fifth resist patterns to form a plurality of sixth resist patterns:

etching the third conductive layer by using ~~the resist pattern~~ the plurality of sixth resist patterns as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing ~~the resist pattern~~ the plurality of sixth resist patterns on the third conductive layer.

17. (Previously Presented) A method of manufacturing a semiconductor device according to claim 16, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

18. (Previously Presented) A method of manufacturing a semiconductor device according to claim 16, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

19. (New). A method for manufacturing a semiconductor device comprising the steps of:
forming a plurality of first resist patterns on an object by discharging a composition under reduced pressure, the composition containing a photosensitizer;
exposing the plurality of first resist patterns with light using a photomask; and
developing the exposed plurality of first resist patterns to form a plurality of second resist patterns.

20. (New) A method for manufacturing a semiconductor device according to claim 19, wherein viscosity of the composition is at most 100 cp.

21. (New) A method for manufacturing a semiconductor device according to claim 19, wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

22. (New) A method for manufacturing a semiconductor device according to claim 19, wherein a wavelength of light is in the range of 350 nm to 450 nm.

23. (New) A method for manufacturing a semiconductor device comprising the steps of:
forming a plurality of first resist patterns on an object by ink jetting under reduced pressure,
wherein each of the plurality of first resist patterns is made of a composition containing a
photosensitizer;

exposing the plurality of first resist patterns with light using a photomask; and
developing the exposed plurality of first resist patterns to form a plurality of second resist
patterns.

24. (New) A method for manufacturing a semiconductor device according to claim 23,
wherein viscosity of the composition is at most 100 cp.

25. (New) A method for manufacturing a semiconductor device according to claim 23,
wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

26. (New) A method for manufacturing a semiconductor device according to claim 23,
wherein a wavelength of light is in the range of 350 nm to 450 nm.

27. (New) A method for manufacturing a semiconductor device comprising the steps of:
forming a plurality of first resist patterns on an object by discharging a composition at
pressure in the range of 1×10^2 Pa to 2×10^4 Pa, the composition containing a photosensitizer;
exposing the plurality of first resist patterns with light using a photomask; and
developing the exposed plurality of first resist patterns to form a plurality of second resist

patterns.

28. (New) A method for manufacturing a semiconductor device according to claim 27, wherein viscosity of the composition is at most 100 cp.

29. (New) A method for manufacturing a semiconductor device according to claim 27, wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

30. (New) A method for manufacturing a semiconductor device according to claim 27, wherein a wavelength of light is in the range of 350 nm to 450 nm.

31. (New) A method for manufacturing a semiconductor device comprising the steps of:
forming a plurality of first resist patterns on an object by ink jetting at pressure in the range of 1×10^2 Pa to 2×10^4 Pa, wherein each of the plurality of first resist patterns is made of a composition containing a photosensitizer;
exposing the plurality of first resist patterns with light using a photomask; and
developing the exposed plurality of first resist patterns to form a plurality of second resist patterns.

32. (New) A method for manufacturing a semiconductor device according to claim 31, wherein viscosity of the composition is at most 100 cp.

33. (New) A method for manufacturing a semiconductor device according to claim 31,

wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

34. (New) A method for manufacturing a semiconductor device according to claim 31,
wherein a wavelength of light is in the range of 350 nm to 450 nm.